W 4A010065E

V_{RRM}	=	650	V
I_F (T_C)	=	19	A
Q_C	=	25	nC

S



Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.27 1.38	1.5 1.6	V	I_F = 10A, T_J = 25 I_F = 10A, T_J = 175	Fig.1
I_R	Reverse Current	6 25	50 200	μA	V_R = 650V, T_J = 25 V_R = 650V, T_J = 175	Fig.2
C	Total Capacitance	640 66 48	/	pF	V_R = 0.1V, T_J = 25 , f = 1MHz V_R = 200V, T_J = 25 , f = 1MHz V_R = 400V, T_J = 25 , f = 1MHz	Fig.5
Q_C	Total Capacitive Charge	25	/	nC	V_R = 400V, I_F = 10A di/dt = 200A/μs, T_J = 25	Fig.4

Thermal Characteristics

	Parameter	S Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1	/W	Fig.6
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	80		

Notes

ADD: No.166 Zhengfang Middle Road, Jiangning District, Nanjing, Jiangsu Province
Contact Person: YONGYANGNAN WANG
TEL 025-68005861, 13770574989

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